

Factory Programmable Oscillator

- Programmed at the Factory and tested at -55 to +125 C
- * Full custom oscillator in 24 hours

Series **CPPM**



Part Numbering Example: CPPM C 7 L Z - A3 B6 - XX.XXXX TS

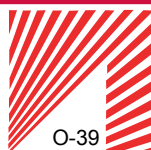
CPPM	C	7	L	Z	A3	B6	XX.XXXX	TS
SERIES	OUTPUT	PACKAGE STYLE	VOLTAGE	ADDED FEATURES	OPERATING TEMP.	STABILITY	FREQUENCY	TRI-STATE
CPPM	C = CMOS T = TTL	5 = 3.2X5 Ceramic 7 = 5X7 Ceramic	Blank = 5V L = 3.3V	Blank = Bulk T = Tube Z = Tape and Reel	A3 = -55°C +125°C	B6 = ± 100 ppm	1.000~133.000 MHz	TS = Tri-State PD=PowerDwn

Specifications:

Description	Min	Typ	Max	Unit
Frequency Range: Programmable to Any Discrete Frequency	1.000		133.000	MHz
Available Stability Options:	-100		100	ppm ppm
Programmable Supply Voltage: (1–133 MHz)	4.5	5.0	5.5	V
(1–133 MHz)	3.0	3.3	3.6	V
Operating Temperature Range Options:	0		+70	°C
	-55		+125	°C
Storage Temperature:	-55		+125	°C
Aging (PPM/Year) Ta=25C, Vdd=5/3.3V			±5	
Programmable Output Level: TTL/CMOS				
Packaging: Tape and Reel (1K per Reel) Tube				

Operating Conditions:

	Description	Min	Max	Unit
Vdd	Supply Voltage	3.0	5.5	V
C _{TTL}	Max Capacitive Load on outputs for TTL levels			
	4.5V–5.5V Vdd ≤ 40 MHz		50	pF
	4.5V–5.5V Vdd > 40–133 MHz		25	pF
C _{CMOS}	Max Capacitive Load on outputs for CMOS levels			
	4.5V–5.5V Vdd, ≤ 66 MHz		50	pF
	4.5V–5.5V Vdd, >66–133 MHz		25	pF
	3.0V–3.6V Vdd, ≤ 40 MHz		30	pF
	3.0V–3.6V Vdd, >40–100 MHz		15	pF



Output Clock Switching Characteristics

Description	TEST CONDITIONS	Min	Typ	Max	Unit
Duty Cycle: TTL @ 1.4 V 4.5-5.5 Vdd	≤ 50 MHz, C _L = 50 pF	45		55	%
	50–66 MHz, C _L = 15 pF	45		55	%
	66–125 MHz, C _L = 25 pF	40		60	%
	125–133 MHz, C _L = 15 pF	40		60	%
Duty Cycle: CMOS @ Vdd/2 4.5-5.5 Vdd 3.0–3.6 Vdd	≤ 66 MHz, C _L ≤ 25 pF	45		55	%
	66–125 MHz, C _L ≤ 25 pF	40		60	%
	125–133 MHz, C _L ≤ 15 pF	40		60	%
	≤ 40 MHz, C _L ≤ 30 pF	45		55	%
	40-100 MHz, C _L ≤ 15 pF	40		60	%
Output Clock Rise/Fall	0.8V–2.0V, 4.5-5.5 Vdd, C _L = 50			1.8	ns
	0.8V–2.0V, 4.5-5.5 Vdd, C _L = 25			1.2	ns
	0.8V–2.0V, 4.5-5.5 Vdd, C _L = 15			0.9	ns
	0.2–0.8Vdd, 4.5-5.5 Vdd, C _L = 50			3.4	ns
	0.2–0.8Vdd, 3.0–3.6 Vdd, C _L = 30			4.0	ns
	0.2–0.8Vdd, 3.0–3.6 Vdd, C _L = 15			2.4	ns
Start Up Time	From power on			10	ms
Power Down Delay Time Synchronous Asynchronous	PWR_DWN pin LOW to output Hi-Z		T/2	T+10	ns
			10	15	ns
Output Disable Time Synchronous Asynchronous	OE pin LOW to output Hi-Z T = Frequency oscillator period		T/2	T+10	ns
			10	15	ns
Output Enable Time				100	n
RMS Period Jitter:	≤ 33.000 MHz		11	13	ps
	> 33.000, MHz		8	11	ps
Peak to Peak	≤ 33.000 MHz		80	110	ps
	> 33.000 MHz		65	80	ps

Electrical Characteristics

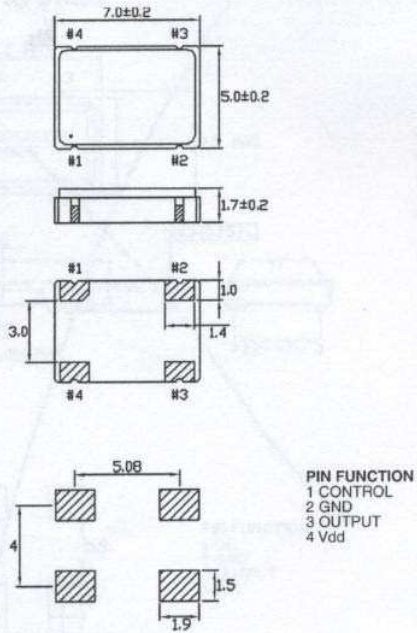
Description	TEST CONDITIONS	Min	Typ	Max	Unit
Input Characteristics (Pin 1): V _{IL} , Low-Level Input Voltage TO TRI-STATE OR POWER DOWN	4.5–5.5V V _{dd} 3.0–3.6V V _{dd}			0.8 0.2V _{dd}	V V
V _{IH} , High-Level Input Voltage TO ENABLE OUTPUT OR OPEN	4.5–5.5V V _{dd} 3.0–3.6V V _{dd}	2.0 0.7V _{dd}			V
I _{IL} , Input Low Current I _{IH} , Input High Current	V _{IN} = 0V V _{IN} = V _{dd}			10 5	μA μA
Output Characteristics: V _{OL} , Low-Level Output Voltage	4.5V–5.5V V _{dd} , 16 mA I _{oL} 3.0V–3.6V V _{dd} , 8 mA I _{oL}			0.4 0.4	V V
V _{OHTTL} , High-level Output Voltage TTL	4.5V–5.5V V _{dd} , -16 mA I _{oL}	2.4			V
V _{OHCOS} , High-level CMOS Voltage	4.5V–5.5V V _{dd} , -16 mA I _{oL} 3.0V–3.6V V _{dd} , -8 mA I _{oL}	V _{dd} -0.4 V _{dd} -0.4			V V
Power Supply Current: (unloaded)	4.5–5.5 V _{dd} , OUTPUT FREQ ≤ 133 MHz 3.0–3.6 V _{dd} , OUTPUT FREQ ≤ 100 MHz			45 25	mA mA
Standby Current:			10	50	μA
Tri State pull up (P_{IN1})	4.5–5.5 V _{dd} , V _{IN} = 0V 4.5–5.5 V _{dd} , V _{IN} = 0.7V	1.1 50	3.0 100	8.0 200	MΩ KΩ
Tri-State Leakage Current	5.0 V _{dd}		20		μA
Output Enable Mode:	Output is Tri-Stated				
Power Down Mode:	Output is Tri-Stated.				

"Tristate internal pull up. Output active when high"

Factory Programmable Oscillator

Note: Bypass Vdd to GND with a 0.01 μ F capacitor

Style 7 5x7 Ceramic SMD



Style 5 3.2x5 Ceramic SMD

